

REMARKS


Claims 1-10 and 20-47 are canceled, leaving claims 11-19 pending in the application. Applicant requests substantive examination of pending claims 11-19.

Respectfully submitted,

Dated: \_\_\_\_\_

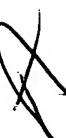
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By: \_\_\_\_\_



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20570" E2E0500T



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No. .... 09/633,556  
priority Filing Date .... August 7, 2000  
Inventor ..... Gurtej S. Sandhu et al.  
Assignee ..... Micron Technology, Inc.  
priority Group Art Unit ..... 2813  
priority Examiner ..... Laura M. Schillinger  
Attorney's Docket No. .... MI22-1896  
Title: Methods of Forming a Nitrogen Enriched Region

**VERSION WITH MARKINGS TO SHOW CHANGES MADE  
ACCOMPANYING PRELIMINARY AMENDMENT**

**In the Specification**

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title is amended as follows: ~~Transistor Structures, Methods of  
Incorporating Nitrogen into Silicon Oxide Containing Layers; and Methods of  
Forming Transistors~~ Methods of Forming a Nitrogen Enriched Region

The following is inserted on p. 1 before the "Technical Field" section,

**CROSS REFERENCE TO RELATED APPLICATION**

This patent resulted from a divisional application of U.S. Patent Application  
Serial No. 09/633,556, which was filed on August 7, 2000.

In the Claims

Claims 1-10 and 20-47 are canceled.

**-END OF DOCUMENT-**

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